



A Product Line of Diodes Incorporated



FZT1053A

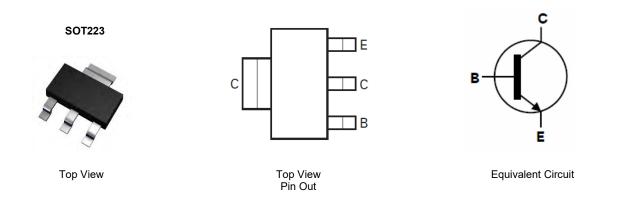
75V NPN MEDIUM POWER HIGH GAIN TRANSISTOR IN SOT223

Features

- BV_{CEO} > 75V
- I_C= 4.5A High Continuous Collector Current
- I_{CM} = 10A Peak Pulse Current
- Low Saturation Voltage V_{CE(sat)} < 120mV @ 1A
- $h_{FE} > 300 @ I_C=1A$ for a High Gain Hold-Up
- R_{CE(sat)} = 78mΩ at 4.5A for a Low Equivalent On-Resistance
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads.
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.112 grams (Approximate)



Ordering Information (Note 4)

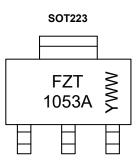
Part Number	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FZT1053ATA	AEC-Q101	FZT1053A	7	12	1,000
Notes: 1 FU Directive 2002/95/FC (RoHS) & 2011/65/FU (RoHS 2) compliant All applicable RoHS exemptions applied					

 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.

3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds

and <1000ppm antimony compounds. 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



FZT 1053A = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5= 2015) WW or $\overline{W}W$ = Week Code (01~53)





Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	150	V
Collector-Emitter Voltage	V _{CEO}	75	V
Emitter-Base Voltage	V _{EBO}	7.0	V
Continuous Collector Current	Ic	4.5	A
Base Current	IB	500	mA
Peak Pulse Current	I _{CM}	10	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		3.0		
Dower Dissinction	(Note 6)		2.0	w	
Power Dissipation	(Note 7)	PD	1.6		
	(Note 8)		1.2	7	
	(Note 5)		41.7		
Thermal Resistance, Junction to Ambient	(Note 6)	R _{0JA}	62.5		
Thermal Resistance, Junction to Amblent	(Note 7)		78.1	°C/W	
	(Note 8)		104		
Thermal Resistance Junction to Lead	(Note 9)	R _{0JL}	10.9		
Operating and Storage Temperature Range	TJ. TSTG	-55 to +150	°C		

ESD Ratings (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes: 5. For a device mounted with the collector lead on 52mm x 52mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

- 6. Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper.
- 7. Same as Note 5, except the device is mounted on 25mm x 25mm 1oz copper.

8. Same as Note 5, except the device is mounted on minimum recommended pad layout.

9. Thermal resistance from junction to solder-point (at the end of the collector lead).

10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.





Thermal Characteristics and Derating Information 10 Ic - Collector Current (A) 3.0 Max Power Dissipation (W) 2.5 52mmX52mm FR4 1 2oz Cu 2.0 1.5 DC 100m 1s 1.0 100ms 10ms 25mmX25mm FR4 1ms 0.5 1oz Cu 100us 10m 0.0 100 120 60 100m 10 40 80 140 160 100 0 20 VCE - Collector Emitter Voltage (V) Temperature (°C) Safe Operating Area **Derating Curve** Single Pulse. T_{amb}=25°C 52mmX52mm FR4 40 Max Power Dissipation (W) Thermal Resistance (°C/W) 52mmX52mm FR4 2oz Cu 100 2oz Cu 30 D=0.5 TTI 20 10 Single Pulse D=0.2 10 <u>| | | ||</u> D=0.05 D=0.1 0 10m 100m 1 10 100 100µ 1m 10m 100m 1 10 100 1k 100µ 1m 1k Pulse Width (s) Pulse Width (s) **Transient Thermal Impedance Pulse Power Dissipation**



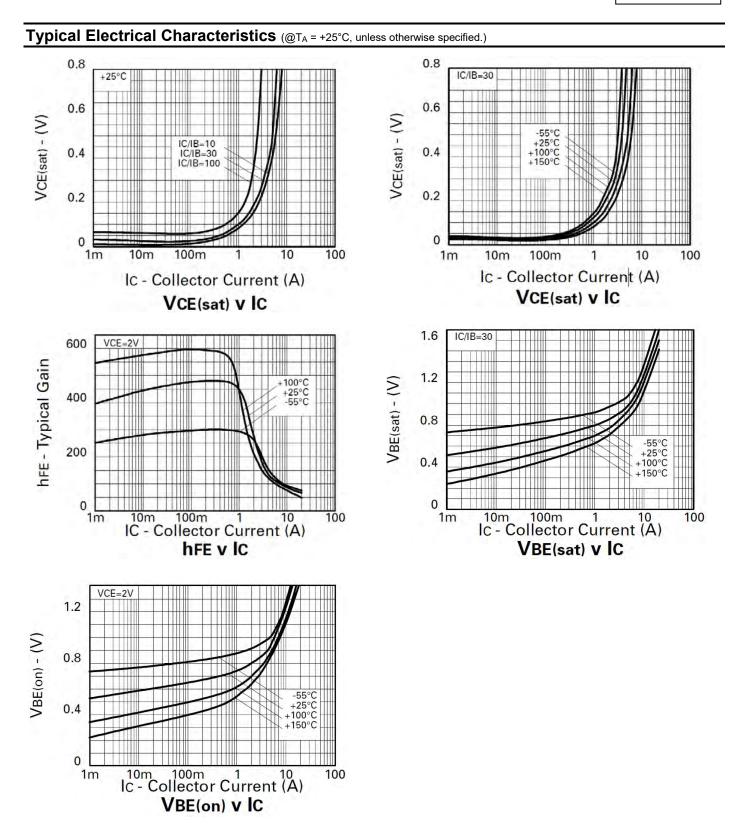


Characteristic	Symbol	Min	Тур.	Мах	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	150	250	-	V	$I_{\rm C} = 100 \mu \text{A}$
Collector-Emitter Breakdown Voltage	BVCES	150	250	-	V	$I_{\rm C} = 100 \mu A$
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CEO}	75	100	-	V	$I_{\rm C} = 10 \text{mA}$
Collector-Emitter Breakdown Voltage	BVCEV	150	250	-	V	I _C = 100µA, V _{EB} = 1V
Emitter-Base Breakdown Voltage	BV _{EBO}	7.0	8.8	-	V	I _E = 100μA
Collector Cutoff Current	ICBO	-	0.9	10	nA	V _{CB} = 120V
Collector Cutoff Current	ICES	-	1.5	10	nA	V _{CES} = 120V
Emitter Cutoff Current	I _{EBO}	-	0.3	10	nA	$V_{EB} = 4V$
		270	440	-		I _C = 10mA, V _{CE} = 2V
	h _{FE}	300	450	1,200		I _C = 0.5A, V _{CE} = 2V
DC current transfer Static Ratio (Note 11)		300	450	-		I _C = 1A, V _{CE} = 2V
		40	60	-		I _C = 4.5A, V _{CE} = 2V
		-	20	-		I _C = 10A, V _{CE} = 2V
		-	21	30		I _C = 0.2A, I _B = 20mA
		-	55	75		I _C = 0.5A, I _B = 20mA
Collector-Emitter Saturation Voltage (Note 11)	V _{CE(sat)}	-	150	200	mV	I _C = 1A, I _B = 10mA
		-	160	210		I _C = 2A, I _B = 100mA
		-	350	440		I _C = 4.5A, I _B = 200mA
Base-Emitter Saturation Voltage (Note 11)	V _{BE(sat)}	-	900	1,000	mV	I _C = 3A, I _B = 100mA
Base-Emitter Turn-On Voltage (Note 11)	V _{BE(on)}	-	825	950	mV	I _C = 3A, V _{CE} = 2V
Transitional Frequency (Note 11)	f⊤	-	140	-	MHz	I _C = 50mA, V _{CE} = 10V, f = 100MHz
Output Capacitance	C _{obo}	-	21	30	pF	V _{CB} = 10V, f = 1MHz,
Switching Time	t _{on}	-	162	-	ns	V _{CC} = 50V, I _C = 2A,
	t _{off}	-	900	-	ns	$I_{B1} = I_{B2} = \pm 20 \text{mA}$

Note: 11. Measured under pulsed conditions. Pulse width = 300 μ s. Duty cycle \leq 2%.





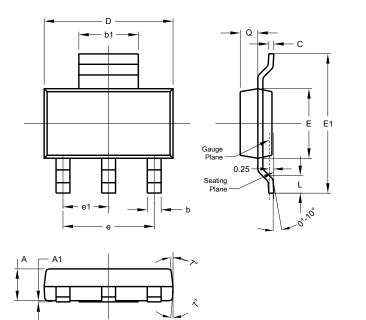






Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



	SOT223					
Dim	Min	Max	Тур			
Α	1.55	1.65	1.60			
A1	0.010	0.15	0.05			
b	0.60	0.80	0.70			
b1	2.90	3.10	3.00			
С	0.20	0.30	0.25			
D	6.45	6.55	6.50			
ш	3.45	3.55	3.50			
E1	6.90	7.10	7.00			
e	-	-	4.60			
e1	-	-	2.30			
L	0.85	1.05	0.95			
Q	0.84	0.94	0.89			
All Dimensions in mm						

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

SOT223

Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00





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